

# MOSFET - Power, Single N-Channel, SUPERFET<sup>®</sup>, FAST, TO247 600 V, 17 mΩ, 75 A

## NTHL017N60S5H

#### Description

The SUPERFET V MOSFET FAST series helps maximize system efficiency by the extremely low switching losses in hard switching application.

#### **Features**

- 650 V @  $T_J = 150^{\circ}C / Typ. R_{DS(on)} = 14.3 \text{ m}\Omega$
- 100% Avalanche Tested
- Pb-Free, Halogen Free / BFR Free and RoHS Compliant

#### **Applications**

- Telecom / Server Power Supplies
- EV Charger / UPS / Solar / Industrial Power Supplies

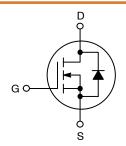
#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		$V_{DSS}$	600	V
Gate-to-Source Voltage	DC	V <sub>GS</sub>	±30	V
	AC (f > 1 Hz)		±30	
Continuous Drain Current	T <sub>C</sub> = 25°C	I <sub>D</sub>	75	Α
	T <sub>C</sub> = 100°C		75	
Power Dissipation	T <sub>C</sub> = 25°C	$P_{D}$	625	W
Pulsed Drain Current (Note 1)	T <sub>C</sub> = 25°C	I <sub>DM</sub>	431	Α
Pulsed Source Current (Body Diode) (Note 1)		I <sub>SM</sub>	431	Α
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Source Current (Body Diode)		I <sub>S</sub>	75	Α
Single Pulse Avalanche Energy	$I_L = 13.2 \text{ A},$ $R_G = 25 \Omega$	E <sub>AS</sub>	1350	mJ
Avalanche Current		I <sub>AS</sub>	13.2	Α
Repetitive Avalanche Energy (Note 1)		E <sub>AR</sub>	6.25	mJ
MOSFET dv/dt		dv/dt	120	V/ns
Peak Diode Recovery dv/dt (Note 2)			20	
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)		T <sub>L</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2.  $I_{SD} \le 37.5 \text{ A}$ , di/dt  $\le 200 \text{ A/}\mu\text{s}$ ,  $V_{DD} \le 400 \text{ V}$ , starting  $T_J = 25^{\circ}\text{C}$ .

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX	
600 V	17 mΩ @ 10 V	75 A	

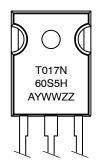


**N-CHANNEL MOSFET** 



TO-247-3LD CASE 340CX

#### MARKING DIAGRAM



T017N60S5H = Specific Device Code

A = Assembly Location YWW = Date Code (Year & Week)

ZZ = Assembly Lot

#### ORDERING INFORMATION

Device	Package	Shipping
NTHL017N60S5H	TO247	30 Units / Tube

#### THERMAL CHARACTERISTICS

Parameter		Value	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	0.2	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	

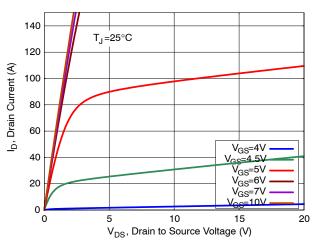
#### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•					
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}, T_J = 25^{\circ}\text{C}$	600	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/ \Delta T_J$	I <sub>D</sub> = 10 mA, Referenced to 25°C	-	630	-	mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 600 V, T <sub>J</sub> = 25°C	-	-	5	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA
ON CHARACTERISTICS	-	•				
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 37.5 \text{ A}, T_J = 25^{\circ}\text{C}$	-	14.3	17.9	mΩ
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 16 \text{ mA}, T_J = 25^{\circ}\text{C}$	2.7	-	4.3	V
Forward Transconductance	9FS	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 37.5 A	-	102	-	S
CHARGES, CAPACITANCES & GATE RE	SISTANCE					
Input Capacitance	C <sub>ISS</sub>	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V}, f = 250 \text{ kHz}$	-	14200	-	pF
Output Capacitance	Coss	]	_	191	-	1
Time Related Output Capacitance	C <sub>OSS(tr)</sub>	$I_D$ = Constant, $V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V	-	3040	-	
Energy Related Output Capacitance	C <sub>OSS(er)</sub>	V <sub>DS</sub> = 0 to 400 V, V <sub>GS</sub> = 0 V	-	322	-	1
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{DD} = 400 \text{ V}, I_D = 37.5 \text{ A},$	-	265	-	nC
Gate-to-Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = 10 V	_	60.5	-	1
Gate-to-Drain Charge	$Q_{GD}$		-	72.7	-	1
Gate Resistance	$R_{G}$	f = 1 MHz	-	1.07	-	Ω
SWITCHING CHARACTERISTICS	-	•				
Turn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS} = 0/10 \text{ V}, V_{DD} = 400 \text{ V},$	-	57.9	-	ns
Rise Time	t <sub>r</sub>	$I_D$ = 37.5 A, $R_G$ = 2.2 $\Omega$	-	22	-	1
Turn-Off Delay Time	t <sub>d(OFF)</sub>	1	-	167	-	1
Fall Time	t <sub>f</sub>		-	4.76	-	1
SOURCE-TO-DRAIN DIODE CHARACT	ERISTICS			-		-
Forward Diode Voltage	V <sub>SD</sub>	$I_{SD} = 37.5 \text{ A}, V_{GS} = 0 \text{ V}, T_{J} = 25^{\circ}\text{C}$	-	-	1.2	V
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V}, I_{SD} = 37.5 \text{ A},$	-	490	-	ns
Reverse Recovery Charge	$Q_{RR}$	dl/dt = 100 A/μs, V <sub>DD</sub> = 400 V	_	11780	-	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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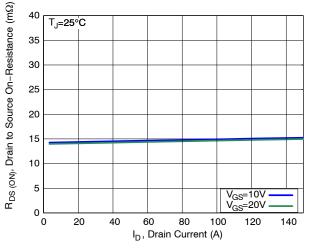
#### **TYPICAL CHARACTERISTICS**



1000 V<sub>DS</sub>=20V 100 T<sub>J</sub>=-55°C T<sub>J</sub>=25°C T<sub>J</sub>=150°C T<sub>J</sub>=150°C V<sub>GS</sub>, Gate to Source Voltage (V)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



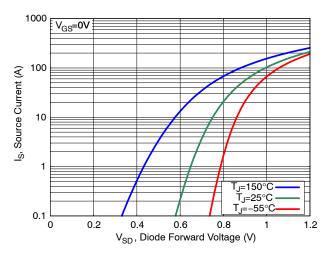
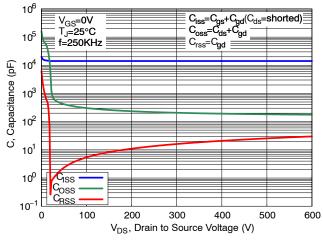


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Diode Forward Voltage vs. Source Current



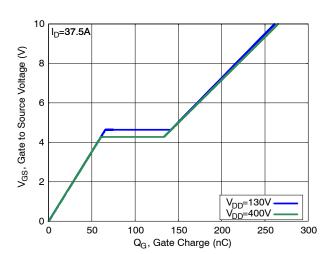


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

#### **TYPICAL CHARACTERISTICS**

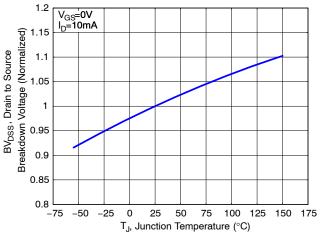
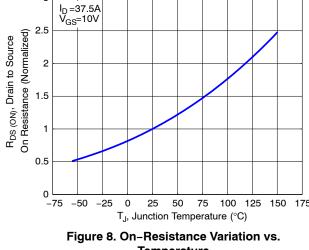


Figure 7. Breakdown Voltage Variation vs. Temperature



**Temperature** 

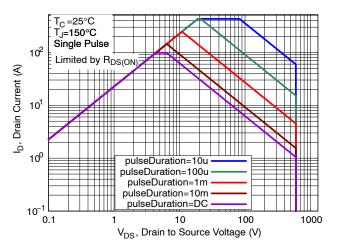


Figure 9. Maximum Safe Operating Area

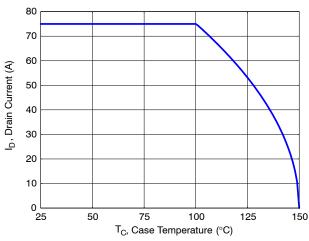


Figure 10. Maximum Drain Current vs. Case **Temperature** 

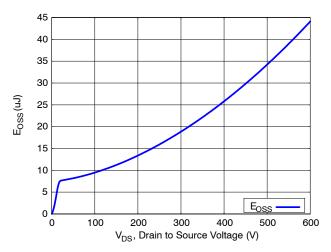


Figure 11. Eoss vs. Drain-to-Source Voltage

#### **TYPICAL CHARACTERISTICS**

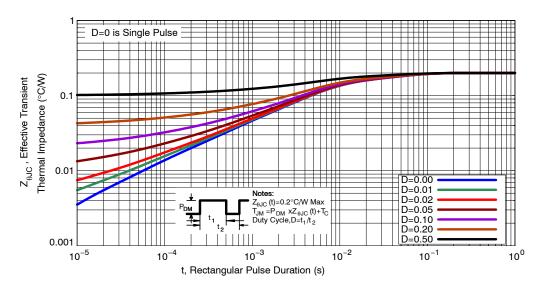
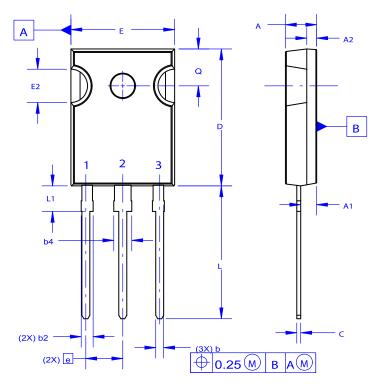


Figure 12. Transient Thermal Impedance

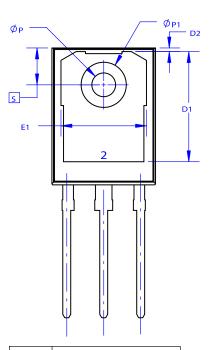
#### **PACKAGE DIMENSIONS**

TO-247-3LD CASE 340CX **ISSUE A** 



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
  D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.



DIM	MIL	LIMETER	S
DIM	MIN	NOM	MAX
Α	4.58	4.70	4.82
<b>A</b> 1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
Е	15.37	15.62	15.87
E2	4.96	5.08	5.20
е	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØΡ	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
С	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

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